

MC74HCT74A

Dual D Flip-Flop with Set and Reset with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

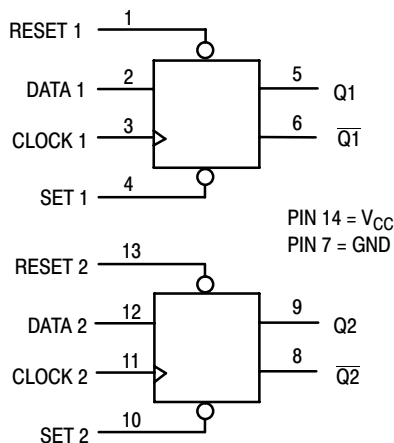
The MC74HCT74A is identical in pinout to the LS74. This device may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

This device consists of two D flip-flops with individual Set, Reset, and Clock inputs. Information at a D-input is transferred to the corresponding Q output on the next positive going edge of the clock input. Both Q and $\bar{Q}$ outputs are available from each flip-flop. The Set and Reset inputs are asynchronous.

Features

- Output Drive Capability: 10 LSTTL Loads
- TTL NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μ A
- In Compliance With the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 136 FETs or 34 Equivalent Gates
- Pb-Free Packages are Available

LOGIC DIAGRAM



Design Criteria	Value	Units
Internal Gate Count†	34	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μ W
Speed Power Product	.0075	pJ

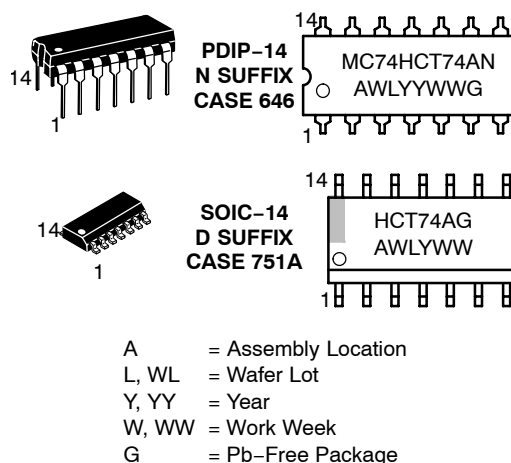
†Equivalent to a two-input NAND gate.



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MARKING DIAGRAMS



PIN ASSIGNMENT

RESET 1	1	14	V _{CC}
DATA 1	2	13	RESET 2
CLOCK 1	3	12	DATA 2
SET 1	4	11	CLOCK 2
Q1	5	10	SET 2
Q1-bar	6	9	Q2
GND	7	8	Q2-bar

FUNCTION TABLE

Inputs				Outputs	
Set	Reset	Clock	Data	Q	Q-bar
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H*	H*
H	H	↗	H	H	L
H	H	↘	L	L	H
H	H	L	X	No Change	No Change
H	H	H	X	No Change	No Change
H	H	↔	X	No Change	No Change

*Both outputs will remain high as long as Set and Reset are low, but the output states are unpredictable if Set and Reset go high simultaneously.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	– 0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	– 0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: –10mW/°C from 65° to 125°C

SOIC Package: –7mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	– 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				– 55 to 25° C	≤ 85° C	≤ 125° C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = 0.1 V or V _{CC} – 0.1 V I _{out} ≤ 20 μA	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V or V _{CC} – 0.1 V I _{out} ≤ 20 μA	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 4.0 mA	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 4.0 mA	4.5	0.26	0.33	0.4	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	±0.1	±1.0	±1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	5.5	2.0	20	80	μA
ΔI _{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs I _{out} = 0 μA	5.5	≥ –55° C	25° C to 125° C		mA
				2.9	2.4		

1. Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0\text{ V} \pm 10\%$, $C_L = 50\text{ pF}$, Input $t_r = t_f = 6.0\text{ ns}$)

Symbol	Parameter	Guaranteed Limit			Unit
		– 55 to 25°C	≤ 85°C	≤ 125°C	
$f_{\max}$	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	30	24	20	MHz
t_{PLH} , t_{PHL}	Maximum Propagation Delay, Clock to Q or $\bar{Q}$ (Figures 1 and 4)	24	30	36	ns
t_{PLH} , t_{PHL}	Maximum Propagation Delay, Set or Reset to Q or $\bar{Q}$ (Figures 2 and 4)	24	30	36	ns
t_{TLH} , t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	15	19	22	ns
C_{in}	Maximum Input Capacitance	10	10	10	pF

2. For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C_{PD}	Power Dissipation Capacitance (Per Enabled Output)*	Typical @ 25°C, $V_{CC} = 5.0\text{ V}$	pF
		32	

3. Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS ($V_{CC} = 5.0\text{ V} \pm 10\%$, $C_L = 50\text{ pF}$, Input $t_r = t_f = 6.0\text{ ns}$)

Symbol	Parameter	Fig.	Guaranteed Limit						Units
			– 55 to 25°C		≤ 85°C		≤ 125°C		
			Min	Max	Min	Max	Min	Max	
t _{su}	Minimum Setup Time, Data to Clock	3	15		19		22		ns
t _h	Minimum Hold Time, Clock to Data	3	3		3		3		ns
t _{rec}	Minimum Recovery Time, Set or Reset Inactive to Clock	2	6		8		9		ns
t _w	Minimum Pulse Width, Clock	1	15		19		22		ns
t _w	Minimum Pulse Width, Set or Reset	2	15		19		22		ns
t _r , t _f	Maximum Input Rise and Fall Times	1		500		500		500	ns

ORDERING INFORMATION

Device	Package	Shipping†
MC74HCT74AN	PDIP–14	25 Units / Rail
MC74HCT74ANG	PDIP–14 (Pb–Free)	
MC74HCT74AD	SOIC–14	55 Units / Rail
MC74HCT74ADG	SOIC–14 (Pb–Free)	
MC74HCT74ADR2	SOIC–14	2500 / Tape & Reel
MC74HCT74ADR2G	SOIC–14 (Pb–Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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SWITCHING WAVEFORMS

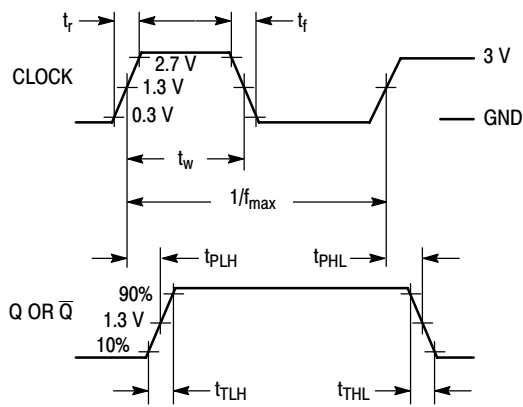


Figure 1.

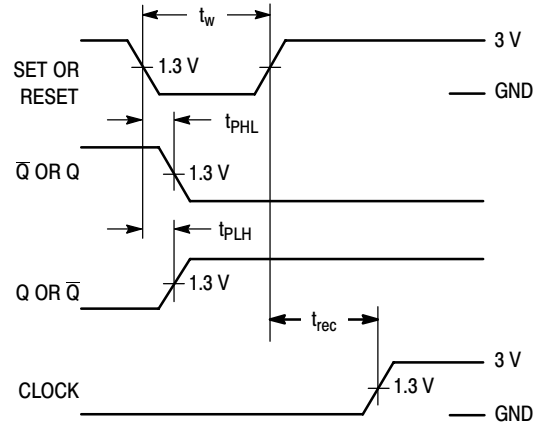


Figure 2.

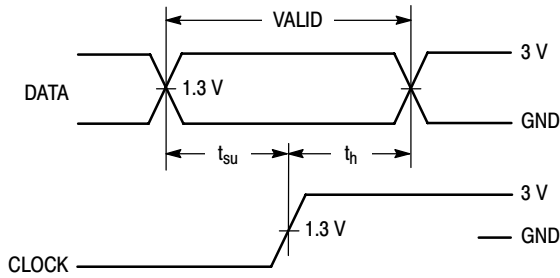
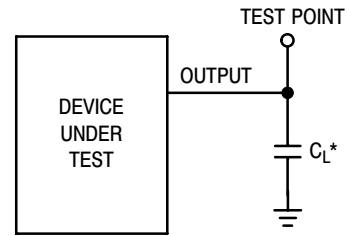


Figure 3.



*Includes all probe and jig capacitance

Figure 5.

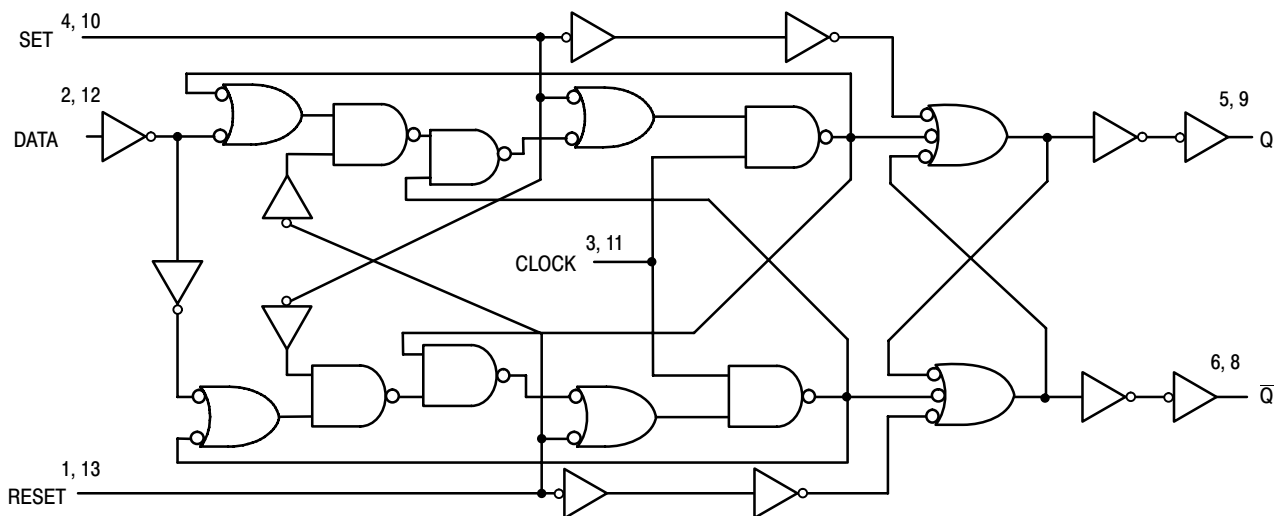
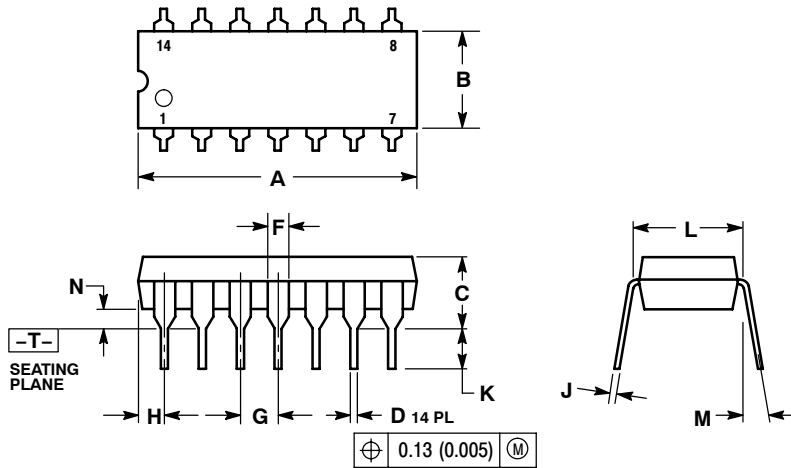


Figure 4. Expanded Logic Diagram

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PACKAGE DIMENSIONS

PDIP-14
CASE 646-06
ISSUE P



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	---	10 °	---	10 °
N	0.015	0.039	0.38	1.01

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9